

**IN THE SPECIFICATION:**

Please replace the paragraph beginning on page 1, line 6 with the following rewritten paragraph:  
--The present application is a continuation of U.S. Application No. 09/903,299, filed Jul. 11, 2001, now U.S. Patent No. 6,656,285, issued December 2, 2003, which is a continuation of U.S. Application No. 09/900,833, filed July 6, 2001, how U.S. Patent No. 6,613,143, issued September 2, 2003.--

Please replace the paragraph beginning on page 6, line 24 with the following rewritten paragraph:  
--The present invention provides a method and apparatus for growing bulk gallium nitride (GaN) or aluminum gallium nitride (AlGaN), preferably using a modified hydride ~~hydride~~ vapor phase epitaxial (HVPE) approach. FIG. 1 is a schematic illustration of a horizontal furnace as used with the invention. It is understood that the invention is not limited to this particular furnace configuration as other configurations (e.g., vertical furnaces) that offer the required control over the temperature, temperature zone or zones, gas flow, source and substrate location, source configuration, etc., can also be used. The furnace configuration illustrated in FIG. 1 is preferred for the growth of undoped GaN as it easily accommodates the desired gallium source of the invention.--